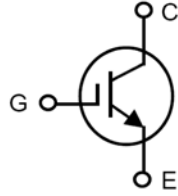


**XPT™ 650V IGBT**  
**GenX3™**
**IXYA50N65C3**  
**IXYP50N65C3**  
**IXYH50N65C3**

 Extreme Light Punch Through  
 IGBT for 20-60kHz Switching


$$V_{CES} = 650V$$

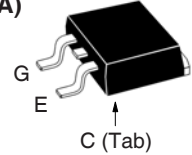
$$I_{C110} = 50A$$

$$V_{CE(sat)} \leq 2.10V$$

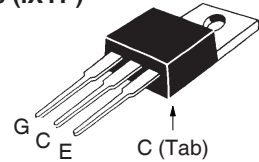
$$t_{fi(typ)} = 26ns$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	650	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	650	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	132	A
$I_{C110}$	$T_C = 110^\circ C$	50	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	250	A
$I_A$	$T_C = 25^\circ C$	25	A
$E_{AS}$	$T_C = 25^\circ C$	400	mJ
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 100$ $V_{CE} \leq V_{CES}$	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 360V$ , $T_J = 150^\circ C$ $R_G = 82\Omega$ , Non Repetitive	8	$\mu s$
$P_C$	$T_C = 25^\circ C$	600	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb
$M_d$	Mounting Torque (TO-247 & TO-220)	1.13 / 10	Nm/lb.in
<b>Weight</b>	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

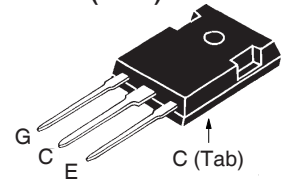
TO-263 (IXYA)



TO-220 (IXYP)



TO-247 AD (IXYH)


 G = Gate      C = Collector  
 E = Emitter    Tab = Collector

**Features**

- Optimized for 20-60kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- International Standard Packages

**Advantages**

- High Power Density
- Extremely Rugged
- Low Gate Drive Requirement

**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- High Frequency Power Inverters

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.5		6.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			15 $\mu A$ 250 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 36A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		1.73 2.10	V V

### Symbol Test Conditions

( $T_J = 25^\circ\text{C}$  Unless Otherwise Specified)

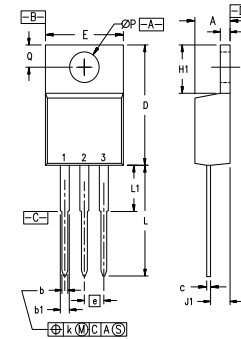
### Characteristic Values

		Min.	Typ.	Max.	
$g_{fs}$	$I_C = 36\text{A}, V_{CE} = 10\text{V}$ , Note 1	18	30		S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2290		pF
$C_{oes}$			135		pF
$C_{res}$			50		pF
$Q_{g(on)}$	$I_C = 36\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		86		nC
$Q_{ge}$			14		nC
$Q_{gc}$			40		nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 36\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		20		ns
$t_{ri}$			36		ns
$E_{on}$			0.80		mJ
$t_{d(off)}$			90		ns
$t_{fi}$			26		ns
$E_{off}$		0.47	0.80		mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 36\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		19		ns
$t_{ri}$			37		ns
$E_{on}$			1.60		mJ
$t_{d(off)}$			113		ns
$t_{fi}$			32		ns
$E_{off}$		0.70		mJ	
$R_{thJC}$				0.25 $^\circ\text{C/W}$	
$R_{thCS}$	TO-220		0.50	$^\circ\text{C/W}$	
$R_{thCS}$	TO-247		0.21	$^\circ\text{C/W}$	

### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (clamp),  $T_J$  or  $R_G$ .

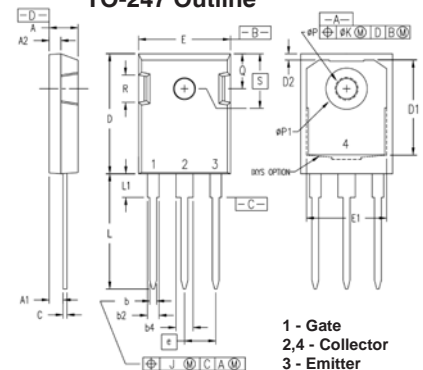
### TO-220 Outline



Pins: 1 - Gate 2 - Collector  
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
$\varnothing P$	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

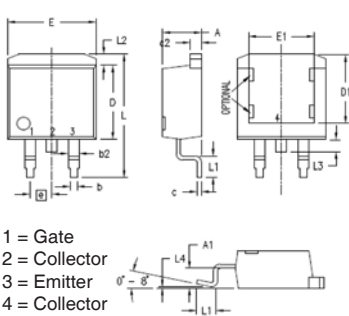
### TO-247 Outline



1 - Gate  
2,4 - Collector  
3 - Emitter

Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.778	0.800
L1	-	4.49	-	0.177
$\varnothing P$	3.55	3.65	0.140	0.144
$\varnothing P1$	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	

### TO-263 Outline



1 = Gate  
2 = Collector  
3 = Emitter  
4 = Collector

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

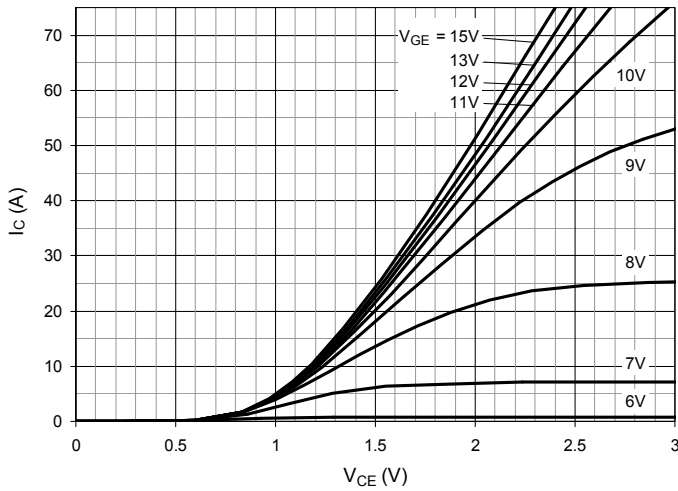


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

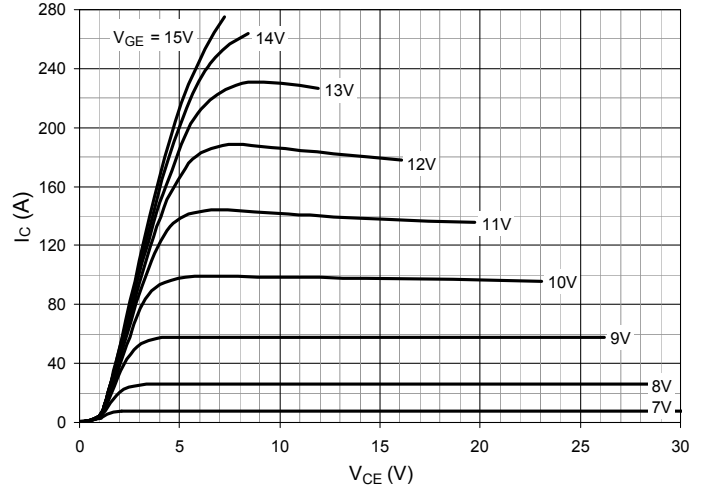


Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$

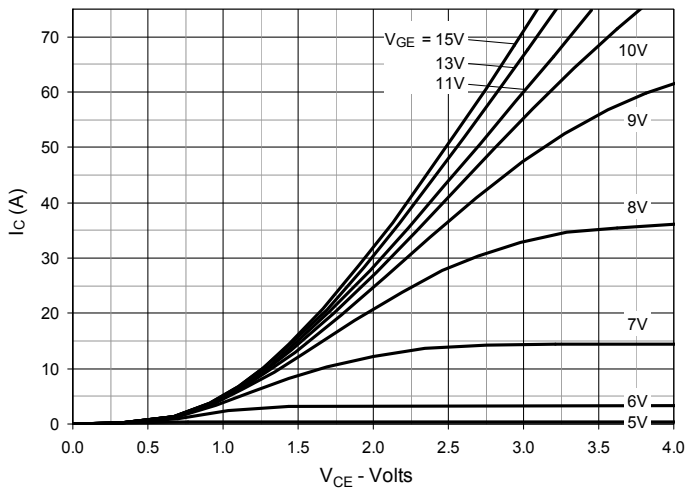


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

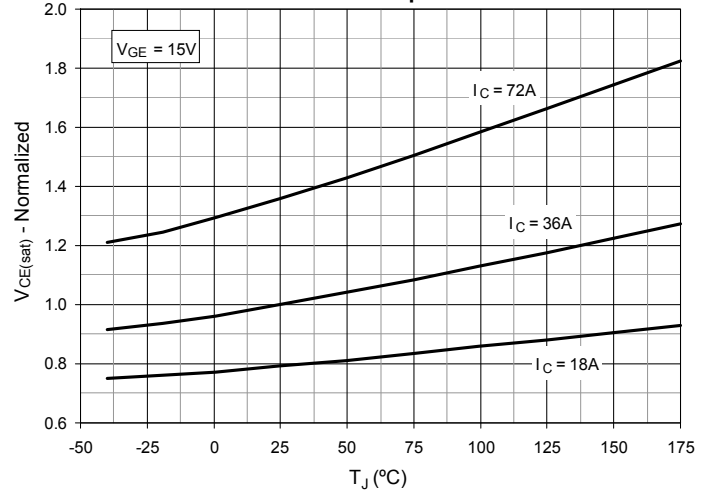


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

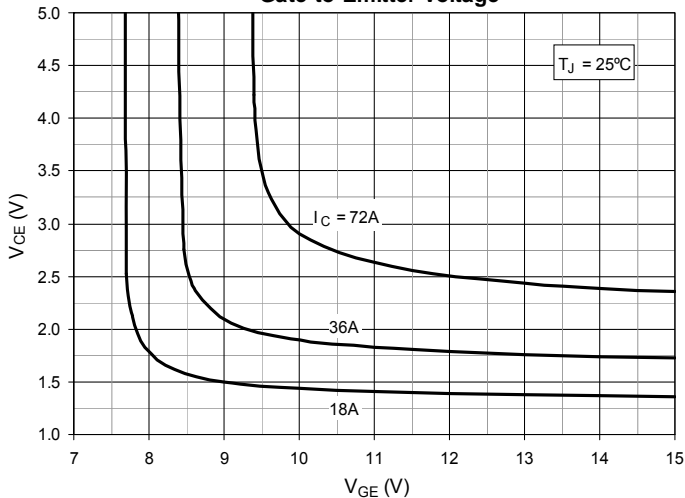


Fig. 6. Input Admittance

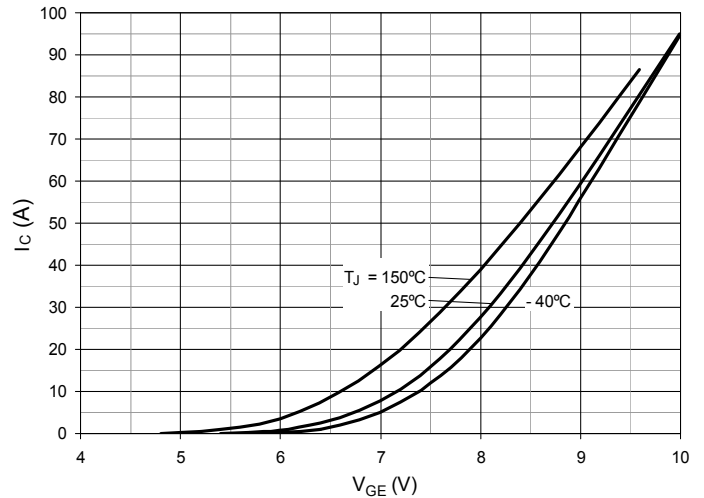


Fig. 7. Transconductance

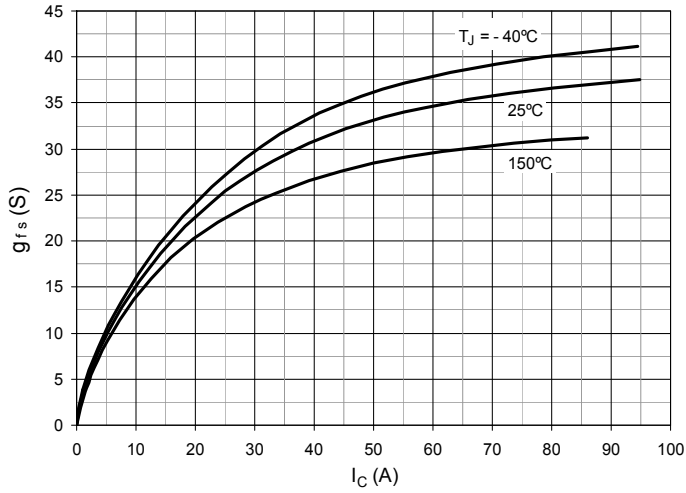


Fig. 8. Gate Charge

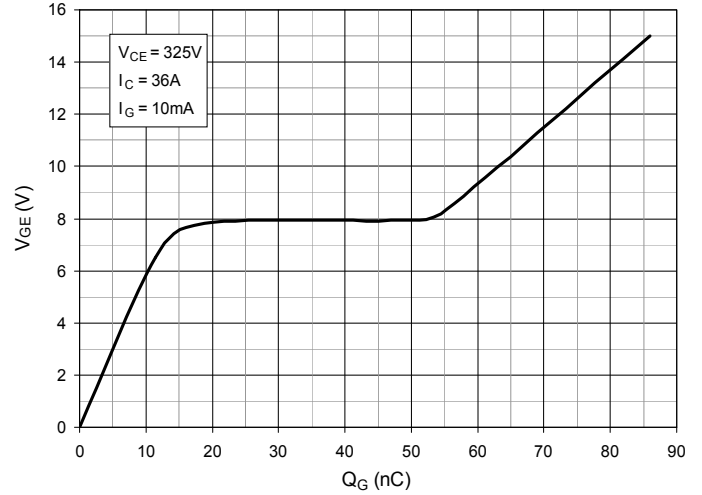


Fig. 9. Capacitance

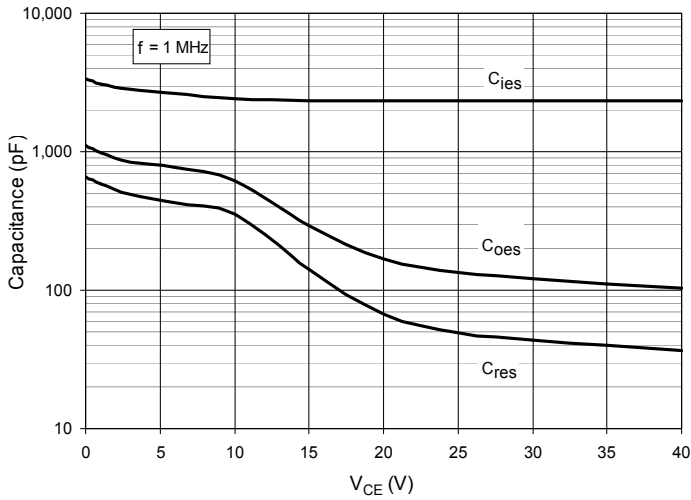


Fig. 10. Reverse-Bias Safe Operating Area

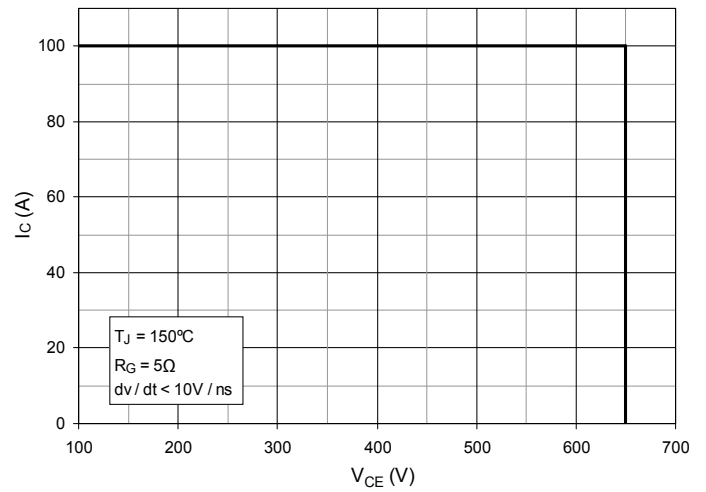


Fig. 11. Forward-Bias Safe Operating Area

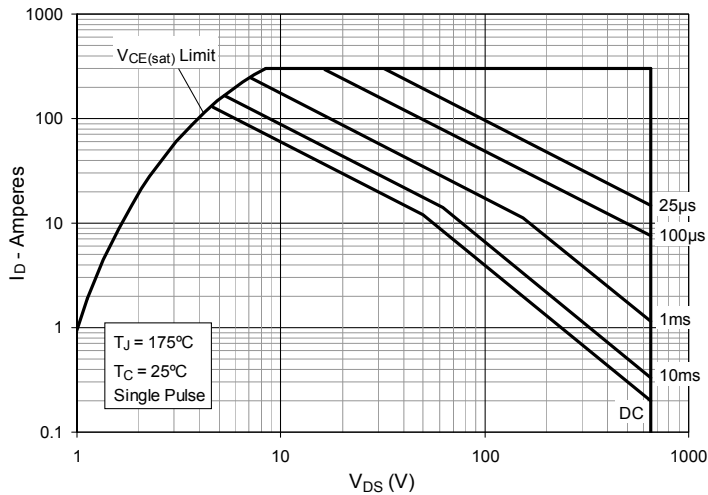
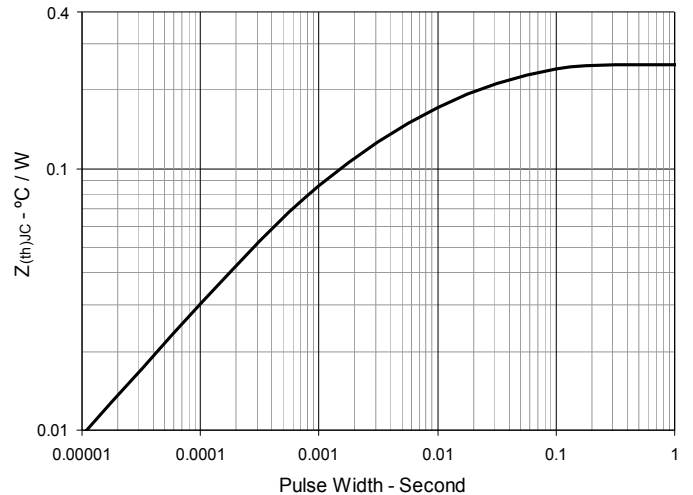
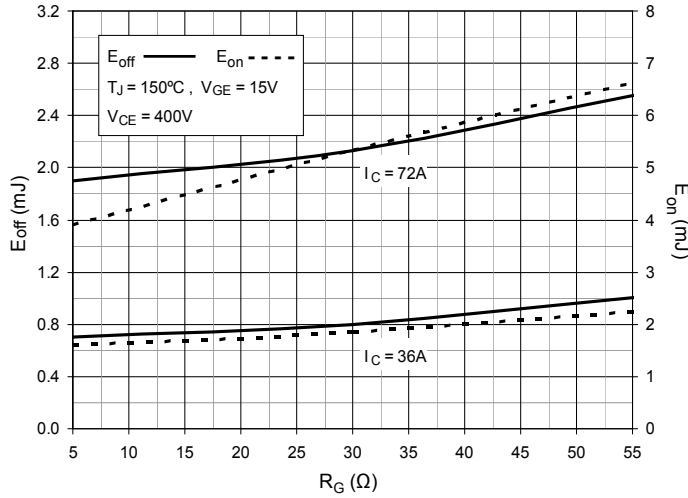


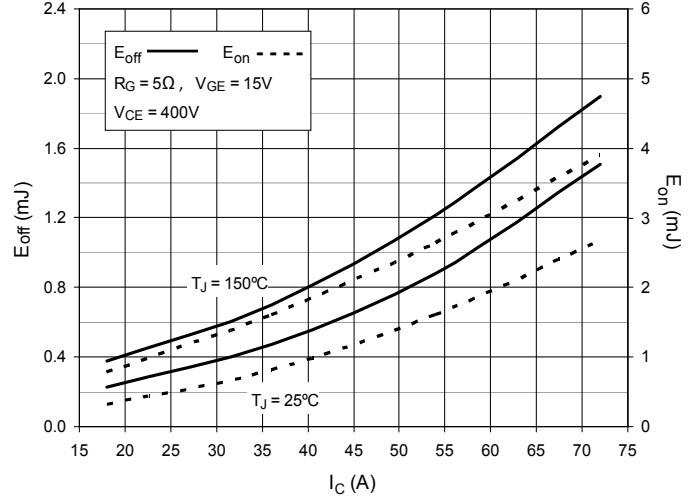
Fig. 12. Maximum Transient Thermal Impedance



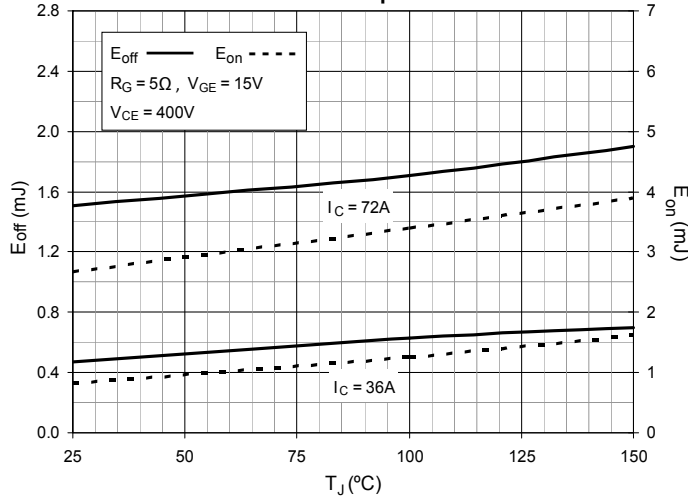
**Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance**



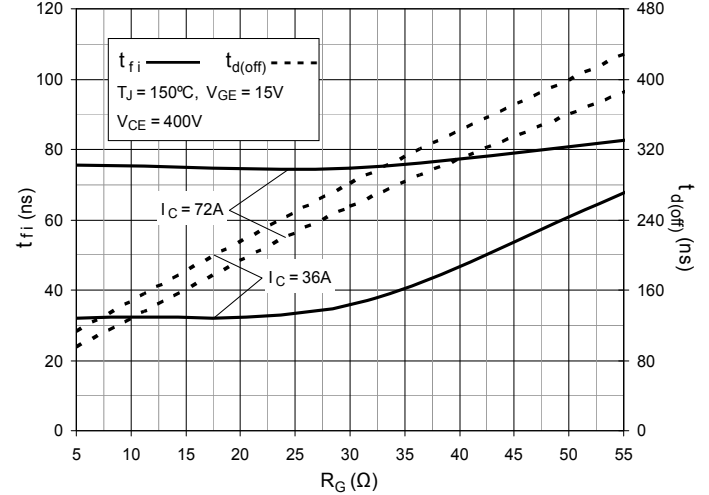
**Fig. 14. Inductive Switching Energy Loss vs. Collector Current**



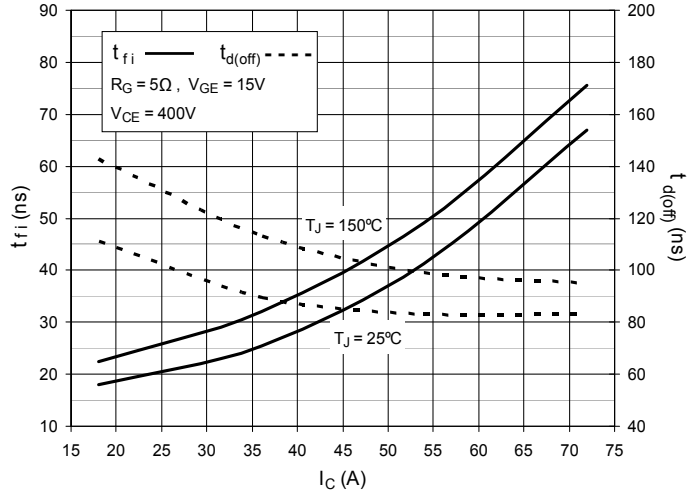
**Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature**



**Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance**



**Fig. 17. Inductive Turn-off Switching Times vs. Collector Current**



**Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature**

